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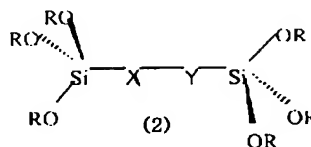
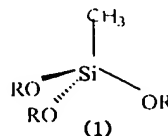
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(54) POLYMETHYLSILSESQUIOXANE COPOLYMER AND PREPARATION THEREOF AND LOW DIELECTRIC COATING MEMBRANE USING THE SAME

(57) Abstract:

PURPOSE: Provided are a soluble polymethylsilsesquioxane copolymer having many terminals and a large molecular weight, a preparation thereof, and a low dielectric coating membrane using the polymethylsilsesquioxane copolymer. **CONSTITUTION:** The polymethylsilsesquioxane is produced by copolymerizing methyltrialkoxo silane represented by the formula 1 with one or two monomers selected from alpha, omega-bis(trialkoxysilyl) compound represented by the formula 2 or bis (methyldimethoxysilyl)ethane in a mixture solvent of an organic solvent and water in the presence of an acid catalyst. The polymethylsilsesquioxane contains the Si-OH terminal content of more than 10%, a molecular weight of 5,000-30,000, and a crosslinkable organic silicon monomer. And the low dielectric coating membrane is formed by mixing the polymethylsilsesquioxane copolymer with a pore generating agent in an organic solvent and then coating the mixture on a substrate. In the formula, R is CH₃- or CH₃CH₂- and -X-Y- is -CH₂-CH₂-.



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Legal Status

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